Docket No.

239499US2/shb

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

Yukio TANIGUCHI, et al.

SERIAL NO:

10/603,821

GAU:

FILED:

June 26, 2003

**EXAMINER:** 

FOR:

CRYSTALLIZATION APPARATUS, OPTICAL MEMBER FOR USE IN CRYSTALLIZATION APPARATUS,

CRYSTALLIZATION METHOD, MANUFACTURING METHOD OF THIN FILM TRANSISTOR, AND

MANUFACTURING METHOD OF MATRIX CIRCUIT SUBSTRATE OF DISPLAY

## **INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97**

COMMISSIONER FOR PATENTS ALEXANDRIA, VIRGINIA 22313

SIR

Applicant(s) wish to disclose the following information.

### REFERENCES

The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed
references are attached, where required, as are either statements of relevancy or any readily available English
translations of pertinent portions of any non-English language references.

A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

#### **RELATED CASES**

Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

# CERTIFICATION

Each item of information contained in this information disclosure statement was first cited in a communication
from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of
this statement.

□ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

## **DEPOSIT ACCOUNT**

Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number <u>15-0030</u>. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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